2.5V Drive Nch MOS FET RTR020N05

●Structure

Silicon N-channel MOS FET

● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT3).
- 3) Low voltage drive (2.5V drive).

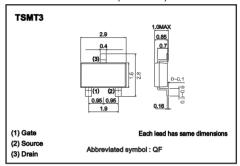
Applications

Switching

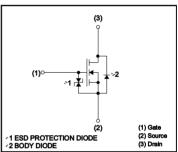
●Packaging specifications and hFE

	Package	Taping
Туре	Code	TL
	Basic ordering unit (pieces)	3000
RTR020N0	0	

■External dimensions (Unit : mm)



●Inner circuit



● Absolute maximum ratings (Ta=25 °C)

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Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	45	٧	
Gate-source voltage		Vgss	12	٧	
Drain current	Continuous	lο	±2.0	Α	
Drain current	Pulsed	IDP ·1	±8	Α	
Source current	Continuous	ls	8.0	Α	
(Body diode)	Pulsed	Isp ·1	8	Α	
Total power dissipation		Po ^{>2}	1.0	w	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

v1 Pw 10μs, Duty cycle 1% v2 Mounted on a ceramic board

●Thermal resistance

		Unit
Channel to ambient Rth(ch	n-a)* 125	°C/W

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	_	10	μA	V _{GS} =12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	45	_	_	٧	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	1	μA	V _{DS} = 45V, V _{GS} =0V
Gate threshold voltage	VGS (th)	0.5	_	1.5	٧	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	RDS (on)	_	130	180	mΩ2	I _D = 2.0A, V _{GS} = 4.5V
		_	135	190	mΩ2	I _D = 2.0A, V _{GS} = 4V
		_	180	250	mΩ2	I _D = 2.0A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs}	1.5	_	_	S	V _{DS} = 10V, I _D = 2.0A
Input capacitance	Ciss	_	200	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	45	-	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	25	-	рF	f=1MHz
Turn-on delay time	t _{d (on)}	_	11	-	ns	V _{DD} ≒ 25V
Rise time	t	_	16	-	ns	lp= 1.0A
Turn-off delay time	td (off) "	_	21	_	ns	Ves= 4.5V R∟=25Ω
Fall time	tr	_	11	_	ns	Rg=10Ω
Total gate charge	Qg	_	2.9	4.1	nC	V _{DD} =25V V _{GS} =4.5V
Gate-source charge	Qgs	_	0.7	–	nC	I _D = 2.0A
Gate-drain charge	Qgd	_	0.9	_	nC	R _L =12.5Ω R _G =10Ω

Pulsed

●Body diode characteristics (Source-drain) (Ta=25^{tt}C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	_	1.2	V	Is= 0.8A, V _{GS} =0V

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